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# 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor Rev. 01 — 11 May 2010

Product data sheet

#### **Product profile** 1.

### 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS8510PA.

#### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

#### **1.3 Applications**

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-100	V
I <sub>C</sub>	collector current		-	-	-2.7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-4	A
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -2.7 A; I <sub>B</sub> = -135 mA	[1] -	110	166	mΩ

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

### 2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	base	
2	emitter	
3	collector	
		1 2 sym013
		Transparent top view

### 3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PBSS9410PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body $2 \times 2 \times 0.65$ mm	SOT1061	

### 4. Marking

Table 4.	Marking codes	
Type num	ıber	Marking code
PBSS941	0PA	AG

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-100	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-100	V
$V_{\text{EBO}}$	emitter-base voltage	open collector	-	-7	V
I <sub>C</sub>	collector current		-	-2.7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-4	A
I <sub>B</sub>	base current		-	-600	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	500	mW
			[2] _	1	W
			[3] _	1.4	W
			[4] _	2.1	W

#### 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

#### Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

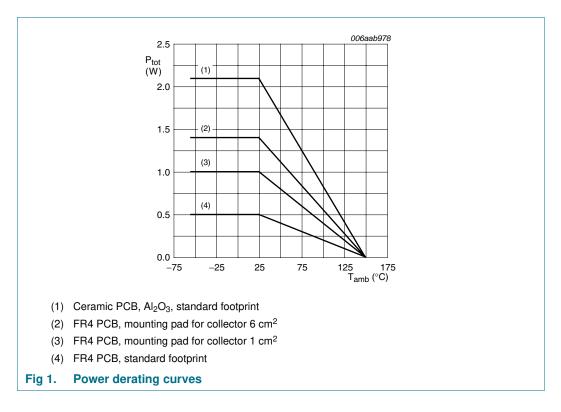
Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



#### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1]</u> _	-	250	K/W
	junction to ambient		[2] _	-	125	K/W
			[3] _	-	90	K/W
			[4]	-	60	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

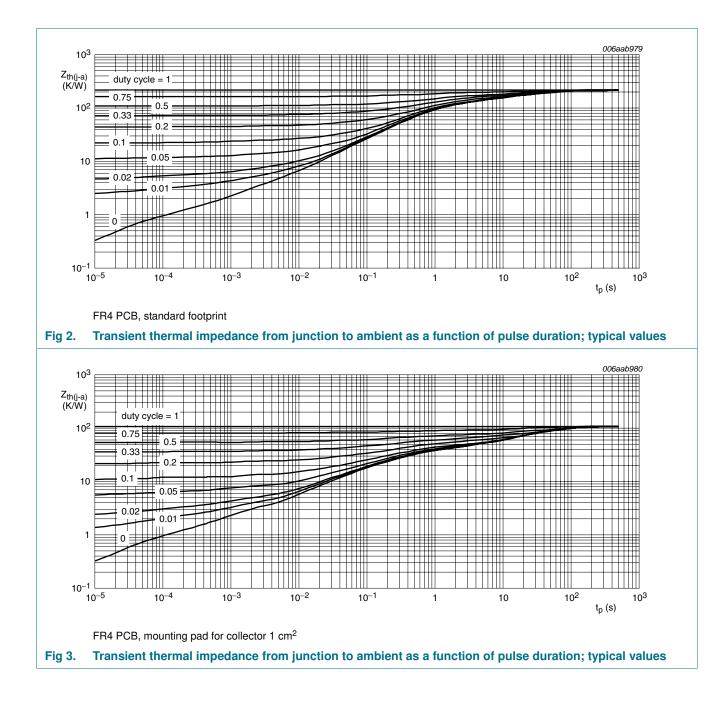
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

PBSS9410PA

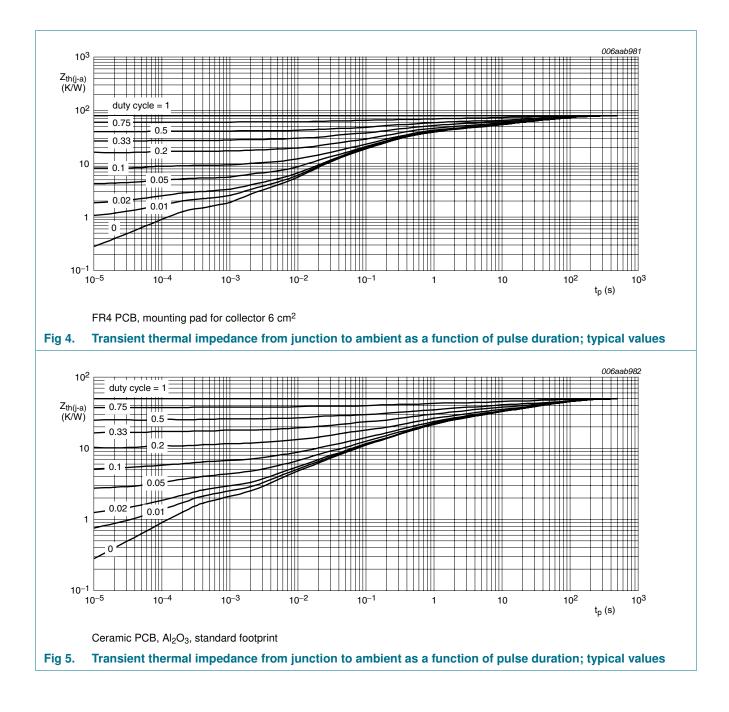
# PBSS9410PA

#### 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor



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#### 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor



100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

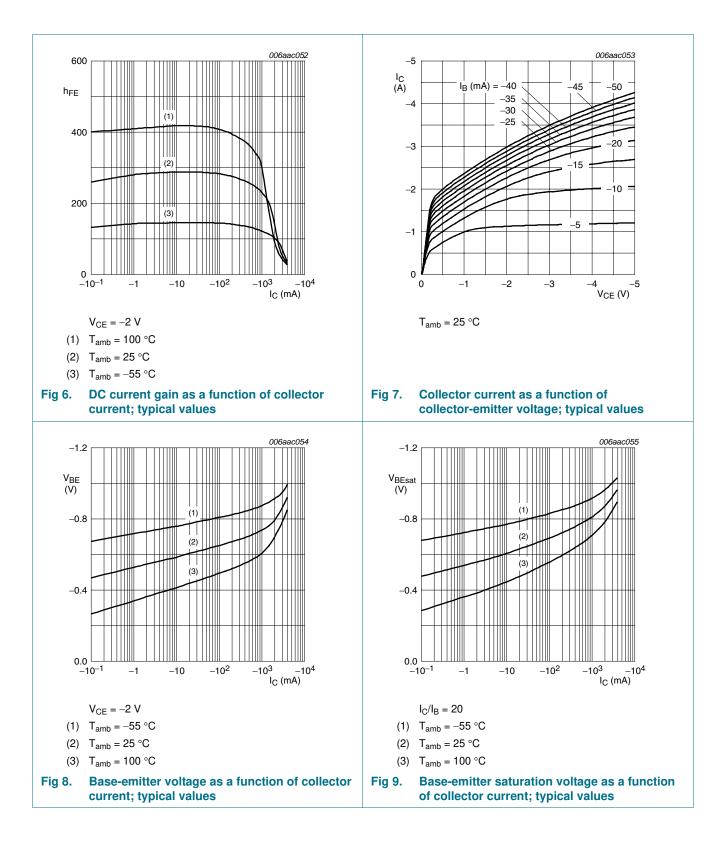
### 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base	$V_{CB} = -80 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	-100	nA
	cut-off current	$\label{eq:VCB} \begin{split} V_{CB} &= -80 \text{ V}; \text{ I}_E = 0 \text{ A}; \\ T_j &= 150 \text{ °C} \end{split}$	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -80 \text{ V};  V_{BE} = 0 \text{ V}$	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 V$	[1]			
		I <sub>C</sub> = -0.5 A	180	295	-	
		$I_{\rm C} = -1$ A	170	260	-	
		$I_{\rm C} = -2$ A	100	150	-	
		I <sub>C</sub> = -3 A	15	25	-	
V <sub>CEsat</sub>		$I_{C} = -0.5 \text{ A}; I_{B} = -50 \text{ mA}$	<u>[1]</u> -	-45	-70	mV
	saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}$	<u>[1]</u> -	-95	-150	mV
		$I_{C} = -2 \text{ A}; I_{B} = -200 \text{ mA}$	<u>[1]</u> -	-125	-185	mV
		$I_{C} = -2.7 \text{ A}; I_{B} = -135 \text{ mA}$	<u>[1]</u> -	-290	-450	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C} = -2.7 \text{ A}; I_{B} = -135 \text{ mA}$	<u>[1]</u> -	110	166	mΩ
V <sub>BEsat</sub>	base-emitter	$I_{C} = -1 \text{ A}; I_{B} = -10 \text{ mA}$	<u>[1]</u> -	-0.75	-0.9	V
	saturation voltage	$I_{C} = -2.7 \text{ A}; I_{B} = -135 \text{ mA}$	[1] -	-0.95	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_C = -2 \text{ A}$	<u>[1]</u> -	-0.75	-0.9	V
t <sub>d</sub>	delay time	$V_{CC} = -9 V; I_C = -2 A;$	-	17	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = -0.1 \text{ A}; I_{Boff} = 0.1 \text{ A}$	-	185	-	ns
t <sub>on</sub>	turn-on time		-	202	-	ns
ts	storage time		-	325	-	ns
t <sub>f</sub>	fall time		-	190	-	ns
t <sub>off</sub>	turn-off time		-	515	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -100 \text{ mA};$ f = 100 MHz	70	115	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	40	50	pF

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# PBSS9410PA

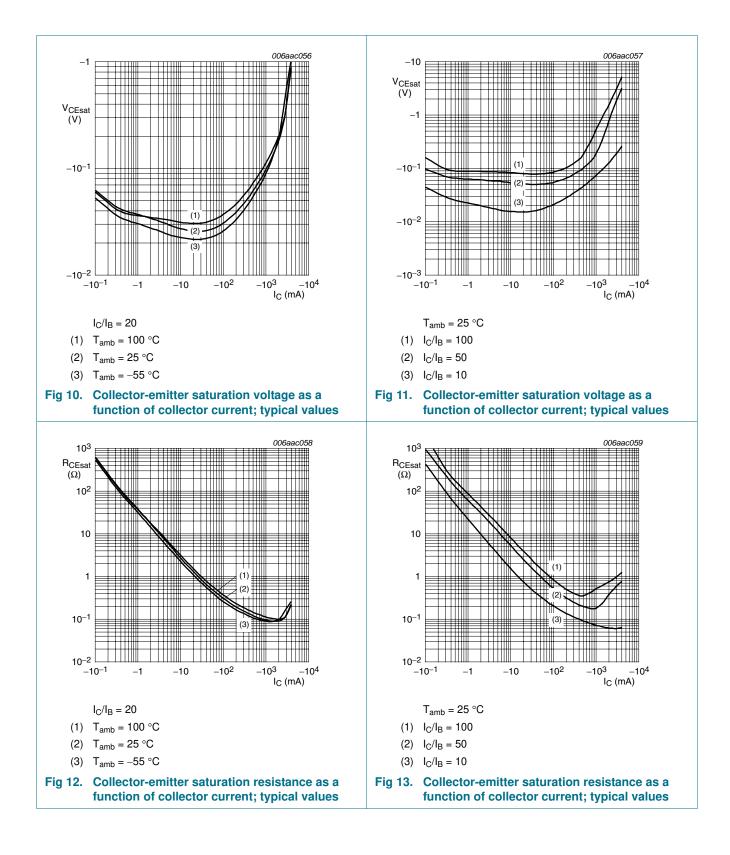
#### 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor



PBSS9410PA

# PBSS9410PA

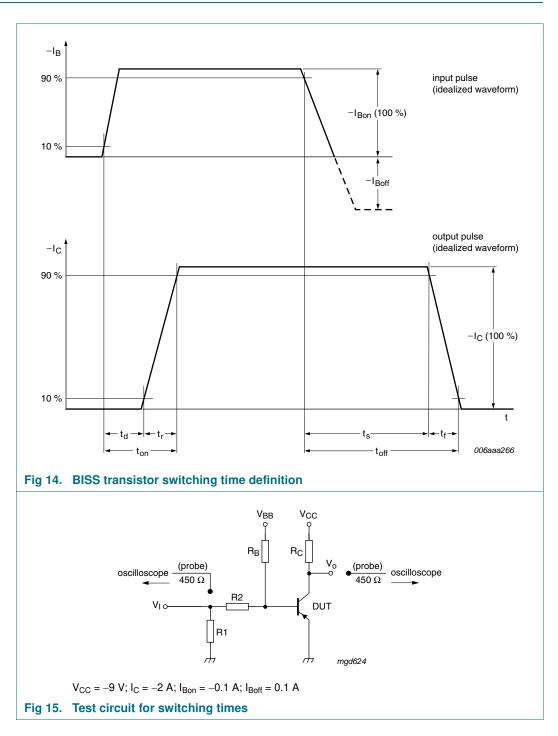
#### 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor



PBSS9410PA

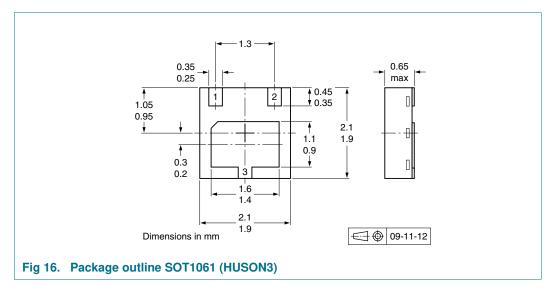
100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

### 8. Test information



100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

### 9. Package outline



### **10. Packing information**

#### Table 8. Packing methods

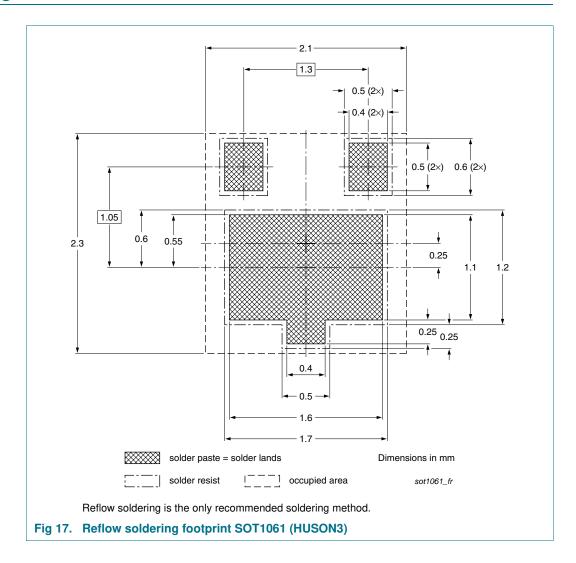
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PBSS9410PA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

### 11. Soldering



PBSS9410PA Product data sheet

11 of 15

100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

### **12. Revision history**

Table 9. Revision hist	Revision history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS9410PA v.1	20100511	Product data sheet	-	-

100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBSS9410PA

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#### 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

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#### 100 V, 2.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

### 15. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 3
7	Characteristics 6
8	Test information 9
9	Package outline 10
10	Packing information 10
11	Soldering 11
12	Revision history 12
13	Legal information
13.1	Data sheet status 13
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks 14
14	Contact information 14
15	Contents 15

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